

H5N2513PL

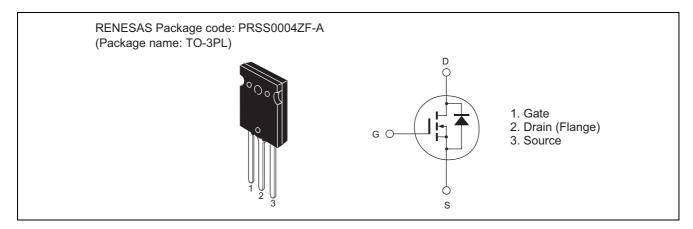
Silicon N Channel MOS FET High Speed Power Switching

REJ03G1243-0100 Rev.1.00 Jul 25, 2008

Features

- Low on-resistance
- High speed switching
- Built-in fast recovery diode

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	250	V
Gate to source voltage	V_{GSS}	±30	V
Drain current	I _D	100	A
Drain peak current	I _{D (pulse)} Note1	400	A
Body-drain diode reverse drain current	I _{DR}	100	A
Body-drain diode reverse drain	I _{DR (pulse)} Note1	400	А
peak current			
Avalanche current	I _{AP} Note3	100	A
Avalanche energy	E _{AR} Note3	625	mJ
Channel dissipation	Pch Note2	250	W
Channel to case thermal impedance	θch-c	0.5	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. Value at Tc = 25°C
- 3. STch = 25° C, Tch $\leq 150^{\circ}$ C

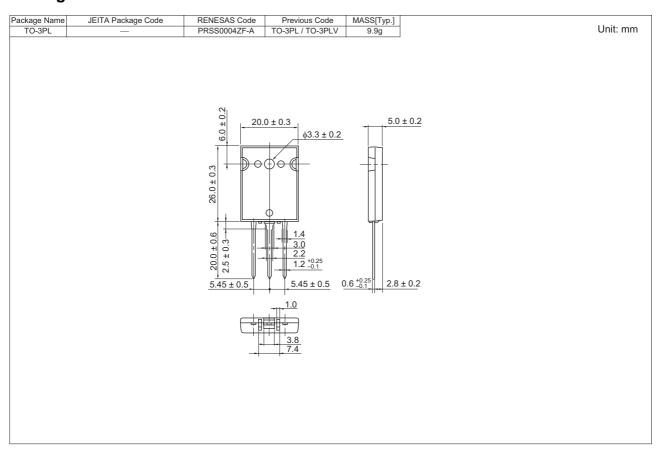
Electrical Characteristics

 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to Source breakdown voltage	$V_{(BR)DSS}$	250	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}		_	10	μΑ	$V_{DS} = 250 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	1	_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	_	4.0	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Forward transfer admittance	y _{fs}	39	65	_	S	$I_D = 50 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Static drain to source on state	R _{DS(on)}	_	0.020	0.026	Ω	$I_D = 50 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
resistance						
Input capacitance	Ciss		9300	_	pF	$V_{DS} = 25 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	1	1200	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	280	_	pF	
Turn-on delay time	t _{d(on)}	_	90	_	ns	$I_D = 50 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time	t _r	_	420	_	ns	$R_L = 2.5 \Omega$, $Rg = 10 \Omega$
Turn-off delay time	$t_{d(off)}$	_	550	_	ns	
Fall time	t _f	_	400	_	ns	
Total gate charge	Qg	_	330	_	nC	$V_{DD} = 200 \text{ V}, V_{GS} = 10 \text{ V}$
Gate to source charge	Qgs	_	45	_	nC	I _D = 100 A
Gate to drain charge	Qgd	_	175	_	nC	
Body-drain diode forward voltage	V_{DF}	_	1.2	1.8	V	I _F = 100 A, V _{GS} = 0 Note4
Body-drain diode reverse recovery	t _{rr}	_	210	_	ns	I _F = 100 A, V _{GS} = 0
time						diF/dt = 100 A/μs

Notes: 4. Pulse test

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
H5N2513PL-E	100 pcs.	Plastic case

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